

參考文獻

- [1]. H.Amano et al. “Stimulated Emission Near Ultraviolet at Room Temperature from a GaN Film Grown on Sapphire by MOVPE Using an AlN Buffer Layer” Jpn.J.Appl.Phys.28,L2112(1989)
- [2]. S. Nakamura, “GaN Growth Using GaN Buffer Layer” Jpn. J. Appl. Phys. 30, L1705 (1991).
- [3]. I. Adesida, A. mahajjn, and E. Andideh, Appl. Phys. Lett. **63**, 2777 (1993)
- [4]. D. A. Stocker, and E. F. Schubert, Appl. Phys. Lett. **73**, 2654 (1998).
- [5]. S. Tripathy, and S. J. Chua, J. Appl. Phys. **91**, 3398 (2001)
- [6]. C. Y. Fang, W. J. Huang, and E. Y. Chang, Jpn. J. Appl. Phys. **42**, 4207 (2003)
- [7]. D. A. Stocker, and E. F. Schubert, Appl. Phys. Lett. **73**, 2654 (1998).
- [8]. M.S. Minsky, M. White, E.L. Hu, Appl. Phys. Lett. 68 (1996) 1531.
- [9]. C. Díaz-Guerra and J. Piqueras” Spatially resolved cathodoluminescence of GaN nanostructures fabricated by photoelectrochemical etching” APL 86, 223103 (2005)
- [10]. C. Youtsey, and I. Adesida, Appl. Phys. Lett. **71**, 2151 (1997).
- [11]. L. H. Peng, and C. W. Chuang, Appl. Phys. Lett. **72**, 939 (1997).
- [12]. J. R. Mileham, S. J. Pearton, C. R. Abernathry, J. D. MacKenzie, R. J. Shul, and S. P. Kilcoyne, Appl. Phys. Lett. **67**, 1119 (1995).
- [13]. C. Youtsey, L. T. Romano, R. J. Molnar, Appl. Phys. Lett. **74**, 3537 (1999).
- [14]. P. Visconti, M. A. Reshchikov, AVS. 19, 1328 (2001)
- [15]. J. A. Grenko, C. L. Reynolds, JAP. 96, 5185 (2004)
- [16]. C. Díaz-Guerra and J. Piqueras, V. Popa, A. Cojocar, and I. M. Tiginyanu, Appl. Phys. Lett. **86**, 223103 (2005).
- [17]. Hock M. Ng, N.G. Weimann, A. Chowdhury, J. Appl. Phys. 94 (2003)650.
- [18]. Hock M. Ng, A. Chowdhury, W. Parz, N.G. Weimann, in: Proceedings of the Electrochemical Society: State-of-the-Art Program on Compound

- Semiconductors XXXIX and Nitride and Wide Bandgap Semiconductors for Sensors, Photonics and Electronics IV, vol. 2003–11, 2003, p. 3.
- [19]. Hock M. Ng, W. Parz, N.G. Weimann, A. Chowdhury, *Jpn. J. Appl. Phys. Part 2* 42 (2003) L1405.
- [20]. O. Ambacher et al., “Two-dimensional electron gases induced by spontaneous and piezoelectric polarization charges in N- and Ga-face AlGaIn/GaN heterostructures,” *Journal of Applied Physics*, Vol 85, Num 6, (3222), 1999.
- [21]. Y. Gao, M. D. Craven, J. S. Speck, *Appl. Phys. Lett.* **84**, 3322 (2004).
- [22]. Robert F. Davis et al., “Pseudo-epitaxial growth and characterization of GaN and related materials on 6H-SiC and Si(111) substrates”
- [23]. Yoshiaki Honda et al. “Crystal Orientation Fluctuation of Epitaxial-Lateral-Overgrown GaN with W Mask Observed by Transmission Electron Diffraction and X-Ray Rocking curves” , *Japan Journal of Applied Physics* Vol.38 pp. L1299~L1302 (1999)
- [24]. Isao KIDOGUCHI et al. “Improvement of Crystalline Quality in GaN Films by Air-Bridged Lateral Epitaxial Growth” , *Japan Journal of Applied Physics* Vol. 39 pp. L453~L456 (2000)
- [25]. J.I. Pankove, *J. Electrochem. Soc.* 119 (1972) 1118.
- [26]. D. Zhuang, J.H. Edgar, “Wet etching of GaN, AlN, and SiC: a review” *Materials Science and Engineering R* 48 (2005) 1–46
- [27]. D.A. Stocker, E.F. Schubert, J.M. Redwing, *Appl. Phys. Lett.* 73 (1998) 2654.
- [28]. C.A. Carosella, B. Molnar, S. Schiestel, J.A. Sprague, *MRS Internet J. Nitride Semicond. Res.* 5S1 (2000) W11.70.
- [29]. A. R. Stonas, P. Kozodoy, *Appl. Phys. Lett.* **77**, 2610 (2000).
- [30]. Yan GAO, Tetsuo FUJII, *JJAP* 2004
- [31]. 高至鈞, 汪建民, 材料分析, 中國材料科學學會, 6 (2004)
- [32]. K. Y. Blohowiak, D. R. Treadwell, and B. L. Muller, *Chem. Mat.* **6**, 2177 (1994)
- [33]. K. Hiramatsu et al. “Recent Progress in Selective Area Growth and Epitaxial Lateral Overgrowth of III-Nitrides: Effects of Reactor Pressure in MOVPE Growth” *phys. stat. sol. (a)* 176, 535 (1999)
- [34]. J. R. Mileham, S. J. Pearton, C. R. Abernathy, J. D. MacKenzie, R. J. Shul, and S. P. Kilcoyne, *Appl. Phys. Lett.* **67**, 1119 (1995).

[35]. H. Miyake, S. Bohyama, *Journal of Crystal Growth* 237–239 (2002)
1055–1059

